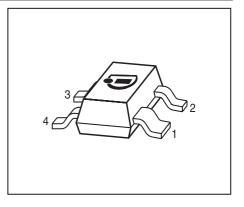


BFP183

Low Noise Silicon Bipolar RF Transistor

- For low noise, high-gain broadband amplifiers at collector currents from 2 mA to 30 mA
- $f_{\rm T}$ = 8 GHz, $NF_{\rm min}$ = 0.9 dB at 900 MHz
- Pb-free (RoHS compliant) package
- Qualification report according to AEC-Q101 available





ESD (Electrostatic discharge) sensitive device, observe handling precaution!

Туре	Marking	Pin Configuration				Package		
BFP183	RHs	1=C	2=E	3=B	4=E	-	-	SOT143

Maximum Ratings at T_A = 25 °C, unless otherwise specified

Parameter	Symbol	Value	Unit
Collector-emitter voltage	V _{CEO}	12	V
Collector-emitter voltage	V _{CES}	20	
Collector-base voltage	V _{CBO}	20	
Emitter-base voltage	V _{EBO}	2	
Collector current	I _C	65	mA
Base current	I _B	5	
Total power dissipation ¹⁾	P _{tot}	250	mW
<i>T</i> _S ≤ 76 °C			
Junction temperature	TJ	150	°C
Storage temperature	T _{Stq}	-55 150	

Thermal Resistance

Parameter	Symbol	Value	Unit
Junction - soldering point ²⁾	R _{thJS}	295	K/W

 ${}^{1}T_{S}$ is measured on the collector lead at the soldering point to the pcb

²For the definition of R_{thJS} please refer to Application Note AN077 (Thermal Resistance Calculation)



Parameter	Symbol	Values			Unit
		min.	typ.	max.	
DC Characteristics			•	•	•
Collector-emitter breakdown voltage	V _{(BR)CEO}	12	-	-	V
<i>I</i> _C = 1 mA, <i>I</i> _B = 0					
Collector-emitter cutoff current	I _{CES}	-	-	100	μA
<i>V</i> _{CE} = 20 V, <i>V</i> _{BE} = 0					
Collector-base cutoff current	I _{CBO}	-	-	100	nA
$V_{\rm CB}$ = 10 V, $I_{\rm E}$ = 0					
Emitter-base cutoff current	I _{EBO}	-	-	1	μA
$V_{\rm EB}$ = 1 V, $I_{\rm C}$ = 0					
DC current gain	h _{FE}	70	100	140	-
$I_{\rm C}$ = 15 mA, $V_{\rm CE}$ = 8 V, pulse measured					

Electrical Characteristics at T_A = 25 °C, unless otherwise specified



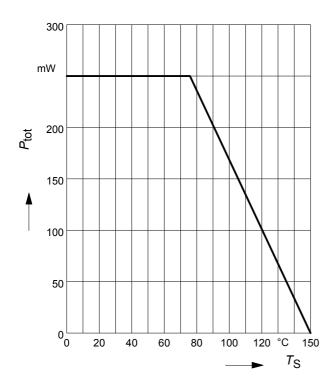
Parameter	Symbol		Unit		
		min.	typ.	max.	
AC Characteristics (verified by random samplin	g)	1	1	1	T
Transition frequency	f _T	6	8	-	GHz
<i>I</i> _C = 25 mA, <i>V</i> _{CE} = 8 V, <i>f</i> = 500 MHz					
Collector-base capacitance	C _{cb}	-	0.3	0.5	pF
$V_{\rm CB} = 10 \text{ V}, f = 1 \text{ MHz}, V_{\rm BE} = 0$,					
emitter grounded					
Collector emitter capacitance	C _{ce}	-	0.27	-	
$V_{\rm CE}$ = 10 V, f = 1 MHz, $V_{\rm BE}$ = 0,					
base grounded					
Emitter-base capacitance	C _{eb}	-	1.1	-]
$V_{\rm EB} = 0.5 \text{ V}, f = 1 \text{ MHz}, V_{\rm CB} = 0$,					
collector grounded					
Minimum noise figure	NF _{min}				dB
$I_{\rm C}$ = 5 mA, $V_{\rm CE}$ = 8 V, $Z_{\rm S}$ = $Z_{\rm Sopt}$,					
<i>f</i> = 900 MHz		-	0.9	-	
<i>f</i> = 1.8 GHz		-	1.4	-	
Power gain, maximum stable ¹⁾	G _{ms}	-	22	-	dB
$I_{\rm C}$ = 15 mA, $V_{\rm CE}$ = 8 V, $Z_{\rm S}$ = $Z_{\rm Sopt}$, $Z_{\rm L}$ = $Z_{\rm Lopt}$,					
<i>f</i> = 900 MHz					
Power gain, maximum available ¹⁾	G _{ma}	-	15.5	-	dB
$I_{\rm C}$ = 15 mA, $V_{\rm CE}$ = 8 V, $Z_{\rm S}$ = $Z_{\rm Sopt}$, $Z_{\rm L}$ = $Z_{\rm Lopt}$,					
<i>f</i> = 1.8 GHz					
Transducer gain	S _{21e} ²				dB
$I_{\rm C}$ = 15 mA, $V_{\rm CE}$ = 8 V, $Z_{\rm S}$ = $Z_{\rm L}$ = 50 Ω ,					
<i>f</i> = 900 MHz		-	17.5	-	
<i>f</i> = 1.8 GHz		-	11.5	-	

Electrical Characteristics at $T_A = 25$ °C, unless otherwise specified

 ${}^{1}G_{\mathsf{ma}} = |S_{21\mathrm{e}} \: / \: S_{12\mathrm{e}}| \: (\mathsf{k}\text{-}(\mathsf{k}^2\text{-}1)^{1/2}), \: G_{\mathsf{ms}} = |S_{21} \: / \: S_{12}|$



Total power dissipation $P_{tot} = f(T_S)$





Package Outline 1±0.1 2.9 ±0.1 0.15 MIN В 0.1 MAX. 1.9 14 2.4 ±0.15 ±12 0.2 0.08...0.15 A 0.8+0.1 0...8 = 0.2 M A 1.7 Note: Mold flash, protrusions or gate burrs of 0,2 mm max. per side are not included SOT143-PO V09 **Foot Print** 0.8 1.2 0.8 6.0 금 0.8 O 1.2 0.8 SOT143-FPR V09 Marking Layout (Example) Type code 2013, June βX % Cinfineon S Date code (Y M) Manufacturer Pin 1 **Standard Packing** Reel ø180 mm = 3.000 Pieces/Reel Reel ø330 mm = 10.000 Pieces/Reel 0.2 \mathbf{m}

1.15

SOT143-TP

3.15

Pin 1





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